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MRF1090MB



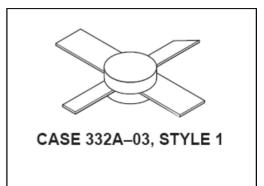
Microwave Pulse Power Silicon NPN Transistor 90W (peak), 960–1215MHz

Rev. V1

Designed for Class B and C common base amplifier applications in short pulse TACAN, IFF, and DME transmitters.

- Guaranteed performance @ 1090 MHz, 50 Vdc Output power = 90 W Peak Minimum gain = 8.4 dB
- 100% tested for load mismatch at all phase angles with 10:1 VSWR
- Industry standard package
- Nitride passivated
- Gold metallized for long life and resistance to metal migration
- Internal input matching for broadband operation

Product Image



MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	70	Vdc
Emitter-Base Voltage	V _{EBO}	4.0	Vdc
Collector-Current — Peak (1)	I _C	6.0	Adc
Total Device Dissipation @ T _C = 25°C (1) (2) Derate above 25°C	PD	290 1.66	Watts W/°C
Storage Temperature Range	T _{stg}	-65 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit	
Thermal Resistance, Junction to Case (3)	R _{eJC}	0.6	°C/W	ĺ

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS					
Collector–Emitter Breakdown Voltage (I _C = 25 mAdc, V _{BE} = 0)	V _(BR) ces	70	_	_	Vdc
Collector–Base Breakdown Voltage (I _C = 25 mAdc, I _E = 0)	V _{(BR)CBO}	70	_	_	Vdc
Emitter–Base Breakdown Voltage (I _E = 5.0 mAdc, I _C = 0)	V _{(BR)EBO}	4.0	_	_	Vdc
Collector Cutoff Current (V _{CB} = 50 Vdc, I _E = 0)	I _{CBO}	_	_	5.0	mAdc
ON CHARACTERISTICS					
DC Current Coin (4)	h	10	20		

DC Current Gain (4)	h _{FE}	10	30	_	_
(I _C = 2.5 Adc, V _{CE} = 5.0 Vdc)					

NOTES:

(continued)

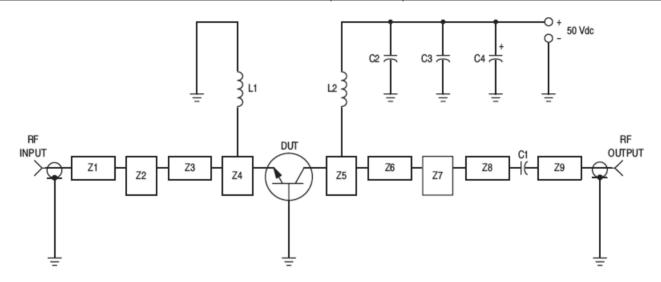
- 1. Pulse Width = 10 μ s, Duty Cycle = 1%.
- 2. This device is designed for RF operation. The total device dissipation rating applies only when the device is operated as an RF amplifier.
- 3. Thermal Resistance is determined under specified RF operating conditions by infrared measurement techniques.
- 4. 80 μs Pulse on Tektronix 576 or equivalent.



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ELECTRICAL CHARACTERISTICS — continued (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
DYNAMIC CHARACTERISTICS					
Output Capacitance (V _{CB} = 50 Vdc, I _E = 0, f = 1.0 MHz)	C _{ob}	_	12	16	pF
FUNCTIONAL TESTS (Pulse Width = 10 μs, Duty Cycle = 1.0%)					
Common–Base Amplifier Power Gain (V _{CC} = 50 Vdc, P _{out} = 90 W pk, f = 1090 MHz)	G _{PB}	8.4	10.8	_	dB
Collector Efficiency (V _{CC} = 50 Vdc, P _{out} = 90 W pk, f = 1090 MHz)	η	35	40	_	%
Load Mismatch (V _{CC} = 50 Vdc, P _{out} = 90 W pk, f = 1090 MHz, VSWR = 10:1 All Phase Angles)	Ψ	No Degradation in Power Output			



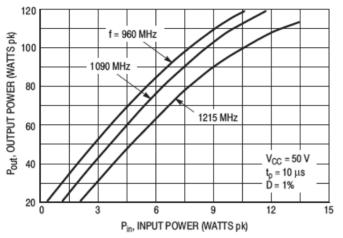
C1, C2 — 220 pF Chip Capacitor, 100–mil ATC
C3 — 0.1 μF
C4 — 47 μF/75 V
L1, L2 — 3 Turns #18 AWG, 1/8″ ID
Z1–Z9 — Distributed Microstrip Elements,

See Photomaster Board Material — 0.031" Thick Glass Teflon, $\varepsilon_{\rm r}$ = 2.5

Figure 1. 1090 MHz Test Circuit



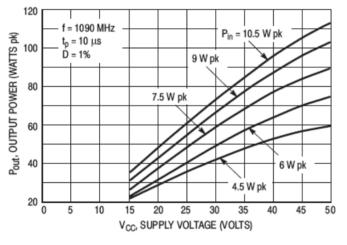
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120 P_{in} = 10.5 W pk Pout, OUTPUT POWER (WATTS pk) 100 9 W pk 80 7.5 W pk 60 6 W pk 4.5 W pk $V_{CC} = 50 \text{ V}$ 40 t_p = 10 μs D = 1% 20 960 1090 1215 f, FREQUENCY (MHz)

Figure 2. Output Power versus Input Power

Figure 3. Output Power versus Frequency



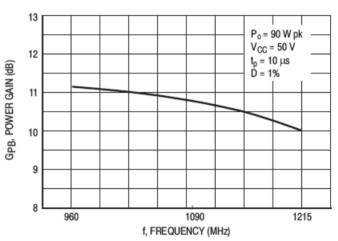
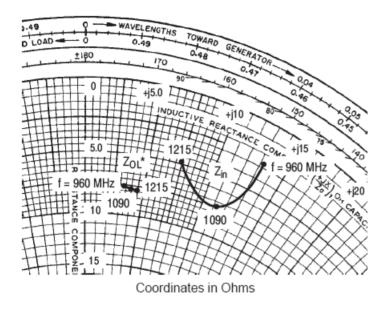


Figure 4. Output Power versus Supply Voltage

Figure 5. Power Gain versus Frequency



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 $P_{out} = 90 \text{ W pk}$ $V_{CC} = 50 \text{ V}$ $t_p = 10 \mu \text{s}$ D = 1%

f	Z _{in}	Z _{OL} *
MHz	Ohms	Ohms
960	2.8 + j13.2	7.6 + j3.5
1090	7.4 + j11.4	7.6 + j4.0
1215	4.7 + j7.5	7.7 + j4.5

Z_{OL}* = Conjugate of the optimum load impedance into which the device output operates at a given output power, voltage, and frequency.

Figure 6. Series Equivalent Input/Output Impedance

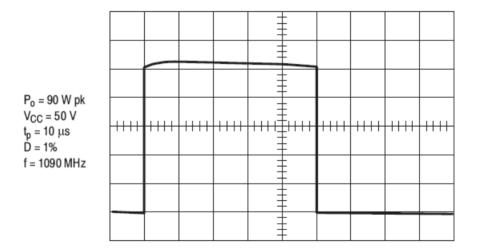
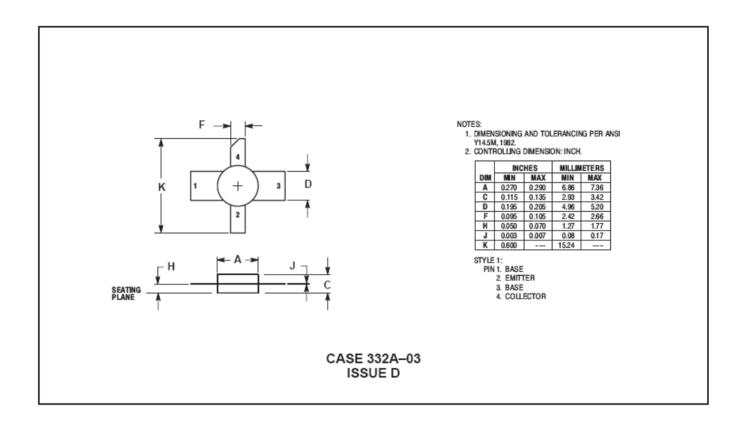


Figure 7. Typical Pulse Performance



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PACKAGE DIMENSIONS



MRF1090MB



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